DECLARATION OF JOINT INVENTORS FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: Methods Of Forming Silicon Dioxide Layers, And Methods Of Forming Trench Isolation Regions, the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations §1.56.

PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful

1	false statement may jeo	pardize the validity of the application or any
2	patent issued therefrom.	
3		* * * * * * * *
4	Full name of inventor:	Sujit Shayan
5	Inventor's Signature:	hand the
6	Date: 7/8/95	
7	Residence: I	Boise, Idaho
8	Citizenship: I	ndia
9	Post Office Address: 5	683 S. Alyssum Place, Boise, ID 83706
10	k	* * * * * * * *
11	Full name of inventor:	Gurtej S. Sandhu
12	Inventor's Signature:	(Tung Sing Rams
13	Date: 7/6/98	\mathcal{J}
,,	Date	
14		oise, Idaho
	Residence: B	oise, Idaho nited Kingdom
14	Residence: B Citizenship: U	
14	Residence: B Citizenship: U	nited Kingdom

1. P. 1. 1.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

<u>Priority</u> Application Serial No	09/497,080		
Priority Filing Date	February 2, 2000		
Inventor			
Assignee	Micron Technology, Inc.		
Priority Group Art Unit	2825		
Priority Examiner	G. Lee		
Attorney's Docket No	MI22-1421		
Title: Methods of Forming Silicon Dioxide Layers, and Methods of Forming			
Trench Isolation Regions			

To:

Mail Stop Patent Application Commissioner for Patents

Art Unit 2825 P.O. Box 1450

Alexandria, VA 22313-1450

From:

David G. Latwesen (Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

ASSOCIATE POWER OF ATTORNEY

Please recognize James E. Lake, whose post office address is 601 W. First Avenue, Suite 1300, Spokane, Washington 99201-3828, as an associate attorney or agent in the above-entitled application.

Date:

David G. Latwesen, Ph.D.

Reg. No. 38,533

EV372452224

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No.

Filing Date
Inventor
Assignee
Assignee
Group Art Unit
Examiner
Attorney's Docket No.

Title: Methods Of Forming Silicon Dioxide Layers, And Methods Of Forming
Trench Isolation Regions

Unknown
Micron Technology, Inc.
Unknown
Unknown
Mi22-826
Title: Methods Of Forming Silicon Dioxide Layers, And Methods Of Forming

POWER OF ATTORNEY BY ASSIGNEE AND CERTIFICATE BY ASSIGNEE UNDER 37 CFR §3.73(b)

To: Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

MICRON TECHNOLOGY, INC., the Assignee of the entire right, title and interest in the above-identified patent application by assignment attached hereto, hereby appoints the attorneys and agents of the firm of WELLS, ST. JOHN, ROBERTS, GREGORY & MATKIN P.S., listed as follows:

Richard J. St. John David P. Roberts Randy A. Gregory Mark S. Matkin James L. Price Deepak Malhotra Mark W. Hendricksen David G. Latwesen George G. Grigel Keith D. Grzelak John S. Reid Lance R. Sadler	Reg. No.	23,032 30,386 32,268 27,376 33,560 32,356 38,533 31,166 37,144 36,369
Lance R. Sadler James D. Shaurette		38,605

EV372452224

and also attorneys Michael L. Lynch (Reg. No. 30,871) and Lia Pappas Dennison (Reg. No. 34,095) of Micron Technology, Inc., as its attorneys with full power of substitution to prosecute this application and transact all business in the Patent and Trademark Office connected therewith.

The Assignee certifies that the above-identified Assignment has been reviewed and to the best of Assignee's knowledge and belief, title is in the Assignee.

Please direct all correspondence regarding this application to:

Wells, St. John, Roberts, Gregory & Matkin P.S. Attn: David G. Latwesen, Ph.D. 601 W. First Avenue, Suite 1300 Spokane, WA 99201-3828

Telephone: (509) 624-4276 Facsimile: (509) 838-3424

MICRON TECHNOLOGY, INC.

Dated: 7-95-1998

Ву:

Title.

M122-826.PAI A279807011336N